

# isc Silicon PNP Power Transistor

#### **DESCRIPTION**

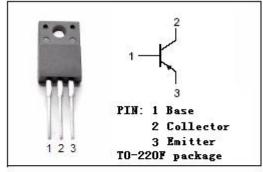
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= -50V(Min)
- · Low Collector Saturation Voltage-
  - : V<sub>CE(sat)</sub>= -0.4V(Max.)@ I<sub>C</sub>= -6A
- Complement to Type 2SD1669
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

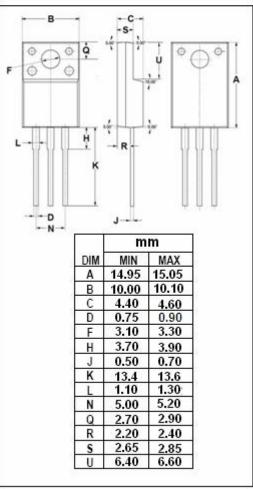


• Designed for relay drivers, high-speed inverters, converters and other general high-current switching applications.

### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-60	V	
Vceo	Collector-Emitter Voltage	-50	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V	
lc	Collector Current-Continuous	-12	Α	
Ісм	Collector Current-Peak	-15	Α	
Pc	Collector Power Dissipation @T <sub>a</sub> =25°C	2	W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	30		
TJ	Junction Temperature 150		$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature	-55~150	${\mathbb C}$	







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2SB1136

### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA; R <sub>BE</sub> = ∞	-50			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>E</sub> = 0	-60			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1mA; I <sub>C</sub> = 0	-6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.6A			-0.4	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -40V; I <sub>E</sub> =0			-100	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4V; I <sub>C</sub> =0			-100	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -2V	70		280	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -5A; V <sub>CE</sub> = -2V	30			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V		10		MHz
Switching Times						
t <sub>on</sub>	Turn-on Time			0.2		μs
t <sub>stg</sub>	Storage Time	$I_{C} = -2A$ , $I_{B1} = -I_{B2} = -0.2A$		0.4		μ <b>S</b>
t <sub>f</sub>	Fall Time			0.1		μS

### ♦ h<sub>FE-1</sub> Classifications

Q	R	S
70-140	100-200	140-280

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